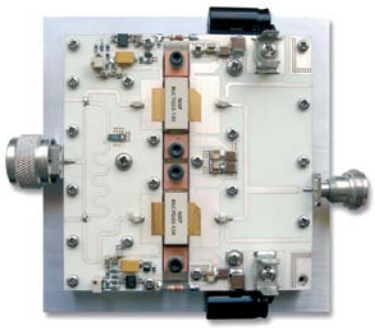
Recommended products

Function	Product	f_{min} (MHz)	f_{max} (MHz)	P1dB (W)	G_p (dB)	Package	Type
HPA	MMIC	920	960	30	29	SOT822-1	BLM6G10-30(G)
	Final	920	960	250	19	SOT502	BLF7G10L(S)-250
		700	1000	80	19	SOT502	BLF8G10L(S)-80
		700	1000	140	19	SOT1204	BLP7G10S-140G
		700	1000	160	19	SOT502	BLF8G10L(S)-160
		500	1000	300	19	SOT1121	BLF6H10L(S)-300P
		700	1000	300	19	SOT539	BLF8G10L(S)-300P
		1805	1880	250	18	SOT539	BLF7G20L(S)-250P
	Integrated Doherty	2010	2025	50	14,5	SOT1130	BLD6G21L(S)-50
	Final	1800	2050	140	19	SOT1204	BLP7G21(S)-140P(G)
	Driver/Final	2110	2170	40	19	SOT1121	BLF6G22L(S)-40P
	Driver	1800	2200	10	19	SOT1179	BLP7G22-10
	Final	2000	2200	160	18	SOT502	BLF7G22L(S)-160
	Driver/Final	2500	2700	40	17,5	SOT1121	BLF6G27L(S)-40P
	Integrated Doherty	2500	2700	50	17,5	SOT1130	BLD7G27S-50
	Final	2500	2700	100	17,5	SOT502	BLF7G27L(S)-100
		2500	2700	140	17	SOT502	BLF7G27L(S)-140
		3400	3600	100	13	SOT502	BLF6G38(LS)-100
		3500	3800	90	13	SOT1246B	BLF7G38LS-90P

Function	Freq band (MHz)	PPEAK (dBm)	POUT-AVG (dBm)	VDS (V)	Gain (dB)	Drain Eff. (%)	Type	Main transistor	Peak transistor
HPA Doherty designs	728-768	58	50	32	20.5	47	SYM	BLF6G10LS-200RN	BLF6G10LS-200RN
	920-960	57.3	49.3	30	16	50	ASYM	BLF8G10LS-160	BLF7G10LS-250
	1476-1511	58.1	49.6	28	16	42	ASYM	BLF7G15LS-200	BLF7G15LS-300P
	1805-1880	58.6	51	28	16	47.6	3-WAY	BLF7G20LS-200	2x BLF7G20LS-200
	1930-1990	58.2	50	28	16	40	SYM	BLF7G20LS-250P	BLF7G20LS-250P
	2110-2170	47	39	28	13	38	SYM	BLD6G22L(S)-50	BLD6G22L(S)-50
	2110-2170	57.2	49.2	28	16	47	3-WAY	BLF7G22LS-160	2x BLF7G22L(S)-160
	2300-2400	55	47.5	28	15.2	44	ASYM	BLF7G24LS-100	BLF7G24LS-140
	2500-2700	50.3	42.3	28	14.5	39	SYM	1/2 BLF7G27LS-90P	1/2 BLF7G27LS-90P
	3400-3600	51	43	28	11.5	32	SYM	BLF6G38-50	BLF6G38-50



Product highlight:
BLF7G27L(S)-100/140

Utilising NXP's Gen7 LDMOS technology, this pair of transistors is designed to give leading performance in 2.7 GHz LTE applications. The BLF7G27L(S)-100 is designed to be the main amplifier, and the BLF7G27L(S)-140 the peak amplifier, in asymmetrical Doherty designs. This pair, along with others at different operational frequencies, are already firm industry favourites with many design wins around the world.

Features

- Asymmetrical Doherty efficiency 37.6% with 15.2 dB gain at 47.5 dB output power
- Capable of 26-32 V operation
- Extremely low thermal resistance
- Consistent device performance
- Unrivalled ruggedness